



Description

The FDFS2P753Z uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



SOP-8

General Features

$V_{DS} = -30V$ $I_D = -5.1A$

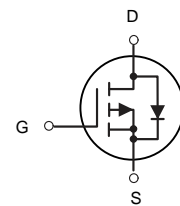
$R_{DS(ON)} < 55m\Omega$ @ $V_{GS} = 10V$

Application

Battery protection

Load switch

Uninterruptible power supply



P-Channel MOSFET

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
FDFS2P753Z	SOP-8	HXY MOSFET	3000

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	- 30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A = 25^\circ C$	Drain Current , $V_{GS} @ 10V$	-5.1	A
IDM	Pulsed Drain Current	-20.4	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation	2.5	W
TSTG	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
Rthj-a	Maximum Thermal Resistance, Junction-ambient	58	°C/W



Electrical Characteristics (T_A=25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -30V, V _{GS} = 0V,	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250μA	-1.0	-1.6	-2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note2</small>	V _{GS} = -10V, I _D = -5A	-	43	55	mΩ
		V _{GS} = -4.5V, I _D = -4A	-	65	90	
C _{iss}	Input Capacitance	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz	-	596	-	pF
C _{oss}	Output Capacitance		-	95	-	pF
C _{rss}	Reverse Transfer Capacitance		-	68	-	pF
Q _g	Total Gate Charge	V _{DS} = -15V, I _D = -5.1A, V _{GS} = -10V	-	6.8	-	nC
Q _{gs}	Gate-Source Charge		-	1	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	1.4	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} = -15V, I _D = -1A, V _{GS} =-10V, R _{GEN} =2.5Ω	-	14	-	ns
t _r	Turn-on Rise Time		-	61	-	ns
t _{d(off)}	Turn-off Delay Time		-	19	-	ns
t _f	Turn-off Fall Time		-	10	-	ns
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-5.1	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-20.4	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = -5.1A	-	-0.8	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%



Typical Electrical and Thermal Characteristics

Figure 1: Output Characteristics

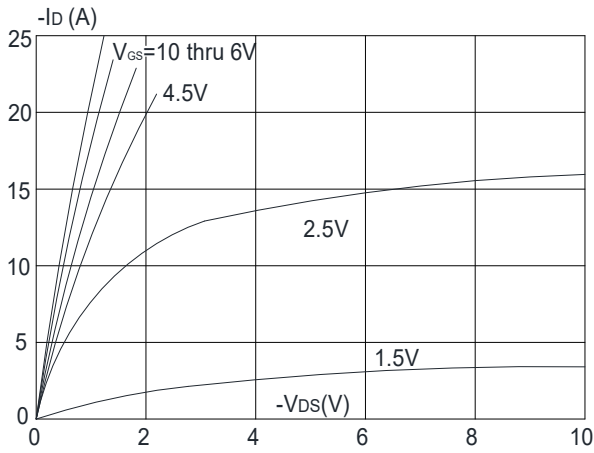


Figure 2: Typical Transfer Characteristics

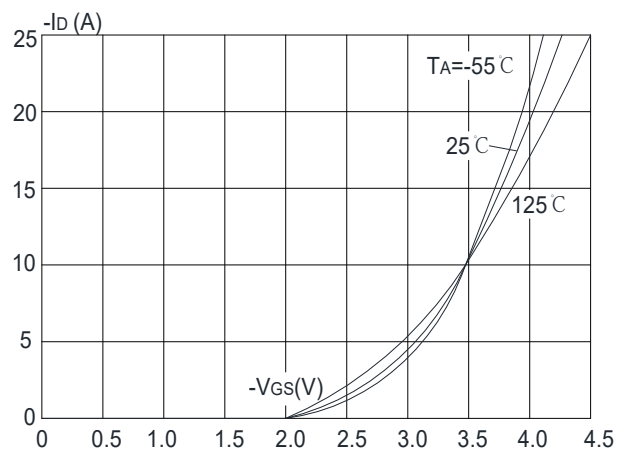


Figure 3: On-resistance vs. Drain Current

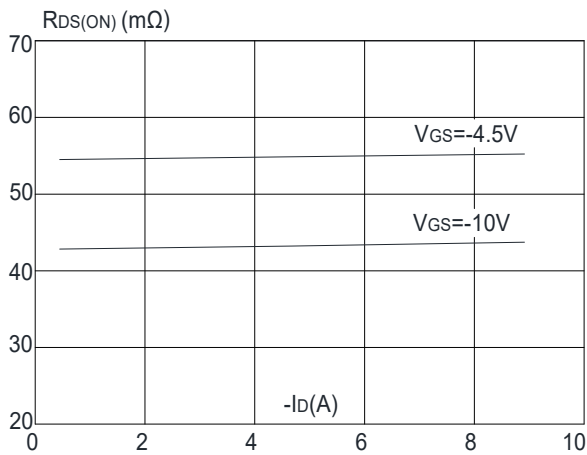


Figure 4: Body Diode Characteristics

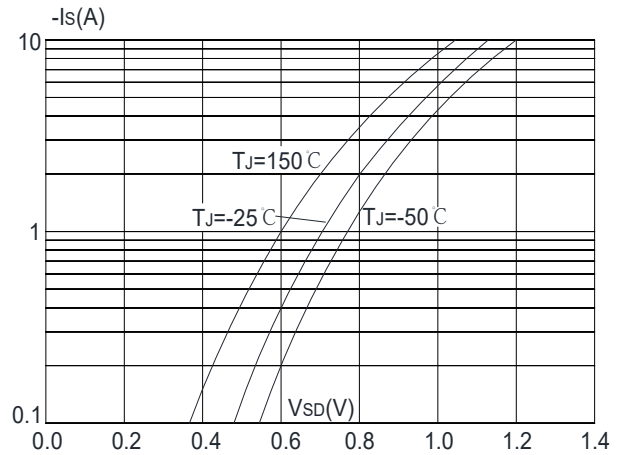


Figure 5: Gate Charge Characteristics

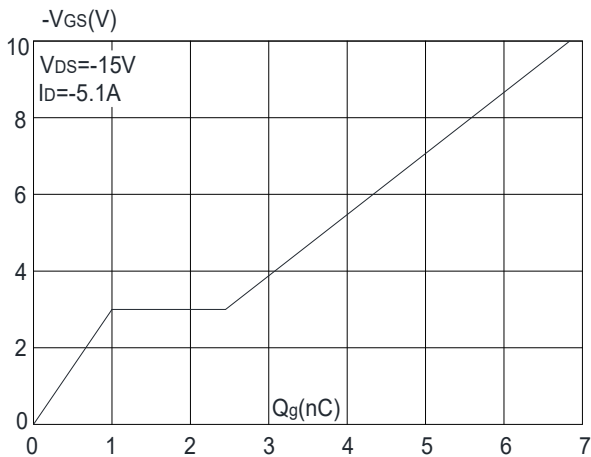


Figure 6: Capacitance Characteristics

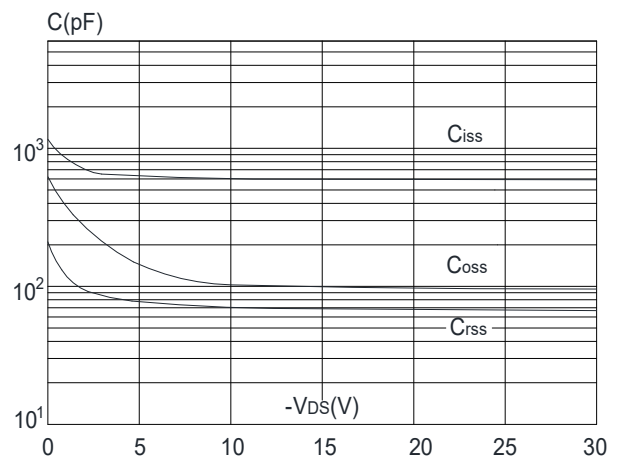




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

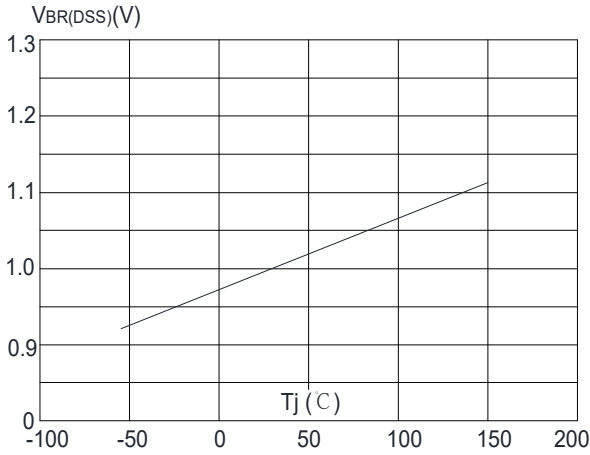


Figure 8: Normalized on Resistance vs. Junction Temperature

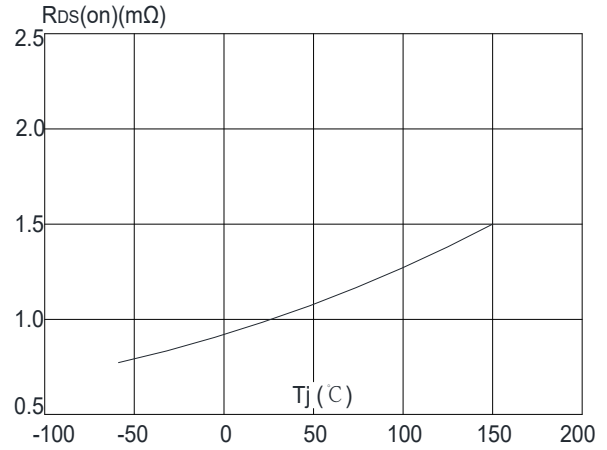


Figure 9: Maximum Safe Operating Area

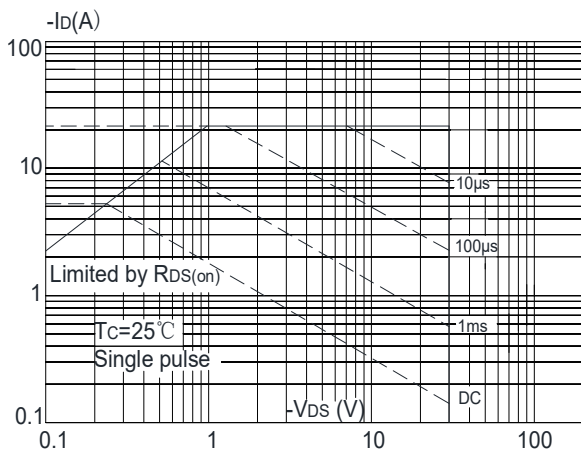


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

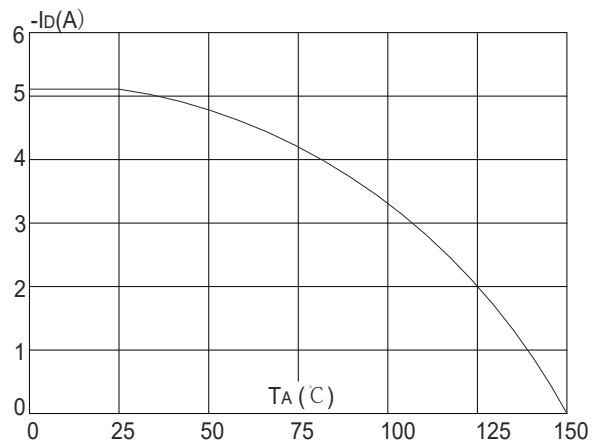
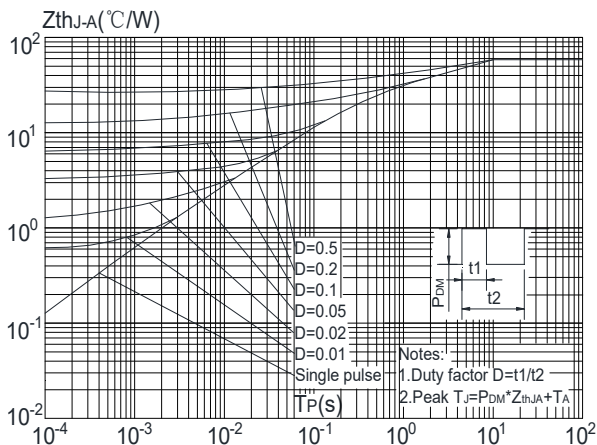


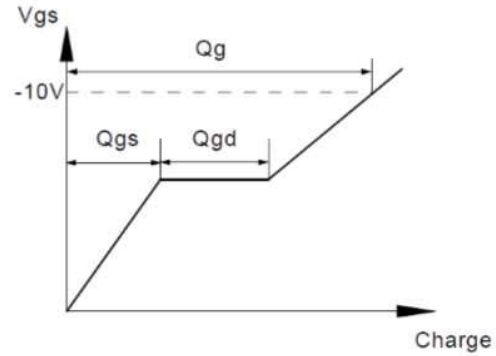
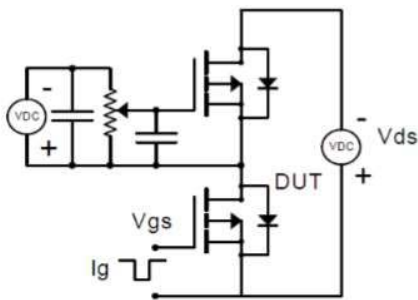
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



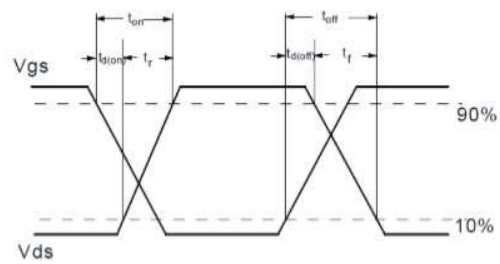
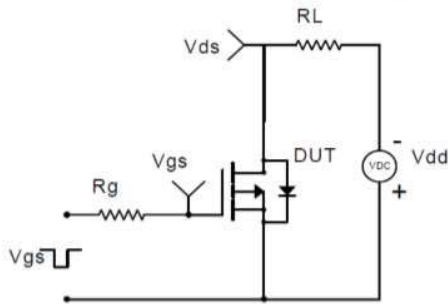


Typical Performance Characteristics

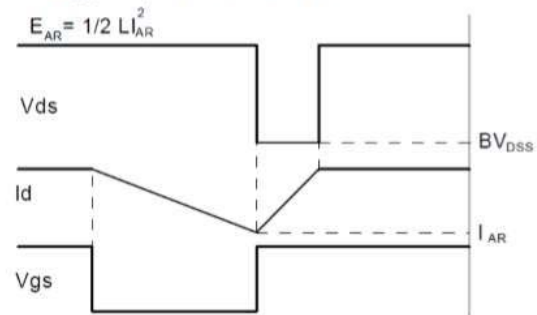
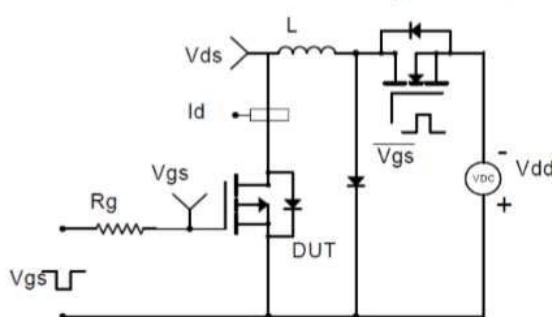
Gate Charge Test Circuit & Waveform



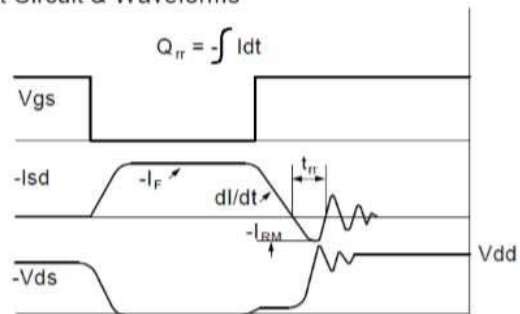
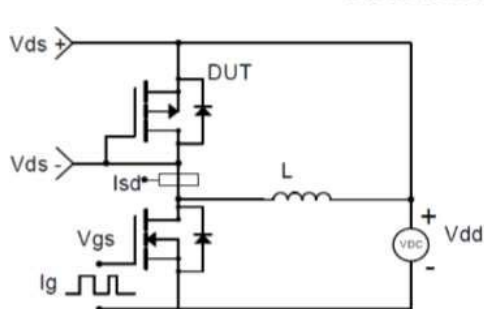
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

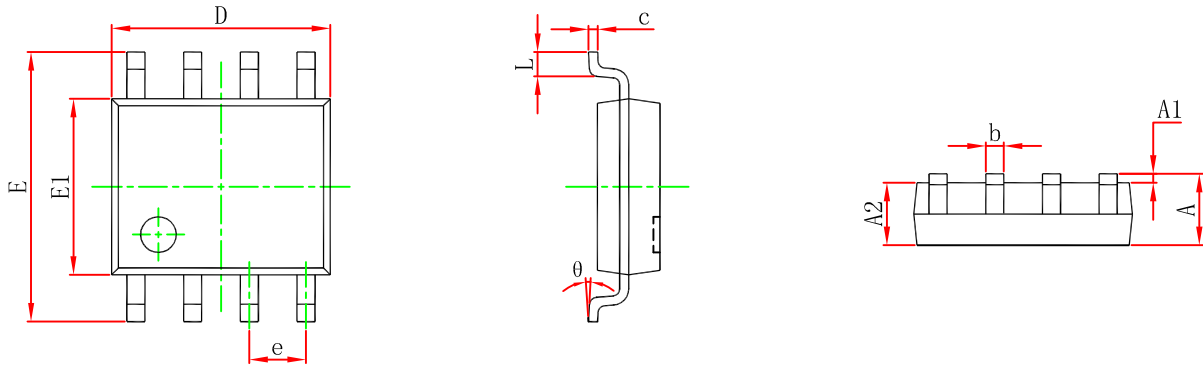


Diode Recovery Test Circuit & Waveforms

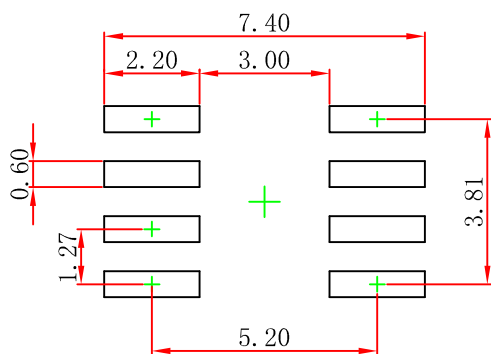




SOP-8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.



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